



SEMICONDUCTOR

## SCHOTTKY BARRIER RECTIFIER

Reverse Voltage - 20 to 200 Volts

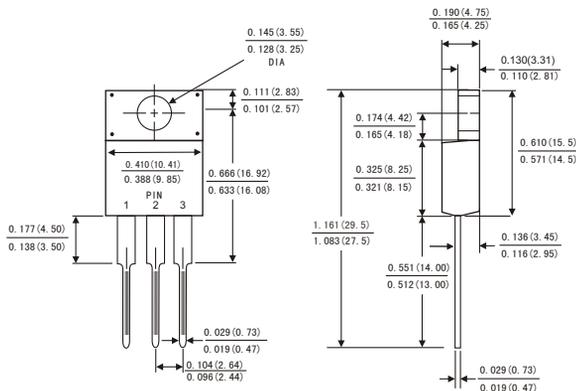
Forward Current - 8.0Amperes

### FEATURES

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,Low forward voltage drop
- Single rectifier construction
- High surge capability
- For use in low voltage ,high frequency inverters, free wheeling ,and polarity protection applications
- High temperature soldering guaranteed:260°C/10 seconds, 0.25"(6.35mm)from case
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



### ITO-220AB



### MECHANICAL DATA

- Case: JEDEC I TO-220AB molded plastic body
  - Terminals: Lead solderable per MIL-STD-750,method 2026
  - Polarity: As marked
  - Mounting Position: Any
- Weight: 0.08ounce, 2.24 gram

Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Ratings at 25°C ambient temperature unless otherwise specified ,Single phase ,half wave ,resistive or inductive load. For capacitive load,derate by 20%.)

	Symbols	SRF 820	SRF 830	SRF 840	SRF 850	SRF 860	SRF 880	SRF 8A0	SRF 8150	SRF 8200	Units
Maximum repetitive peak reverse voltage	$V_{RRM}$	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	$V_{RMS}$	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage	$V_{DC}$	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current (see Fig.1)	$I_{(AV)}$	8.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	$I_{FSM}$	150.0									Amps
Maximum instantaneous forward voltage at 8.0 A(Notes 1)	$V_F$	0.60			0.75		0.85		0.90	0.95	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Notes 1)	$T_a = 25^\circ C$	15									mA
	$T_a = 125^\circ C$										
Typical thermal resistance (Notes 2)	$R_{\theta JC}$	2.5									°C/W
Operating junction temperature range	$T_J$	-65 to +125				-65 to +150					°C
Storage temperature range	$T_{STG}$	-65 to +150									°C

- Notes: 1.Pulse test: 300 μs pulse width,1% duty cycle  
2.Thermal resistance from junction to case

# RATINGS AND CHARACTERISTIC CURVES SRF820-SRF8200

FIG.1-FORWARD CURRENT DERATING CURVE

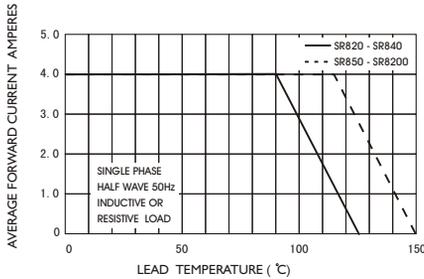


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

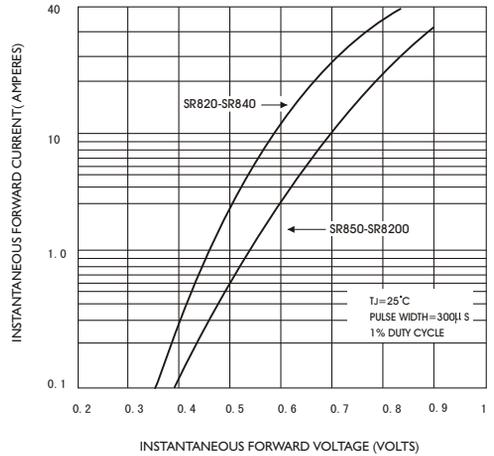


FIG.4-TYPICAL JUNCTION CAPACITANCE

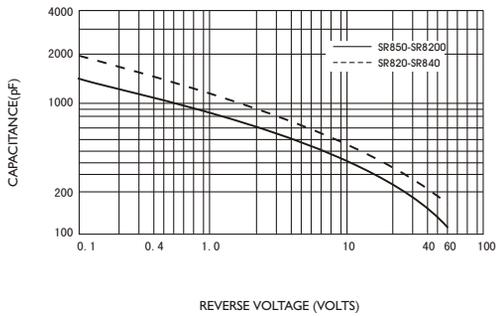


FIG.3-TYPICAL REVERSE CHARACTERISTICS

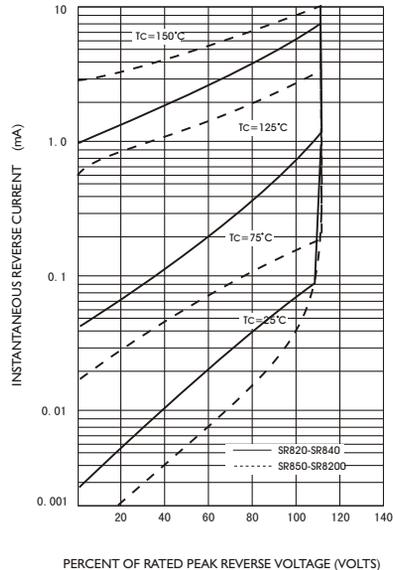


FIG.5-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

